



30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C	
30V	$1.6 m\Omega$ @ $V_{GS} = 10V$	100A	

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

Applications

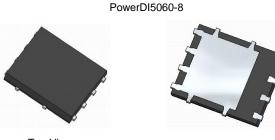
- DC-DC Converters
- Load Switch

Features

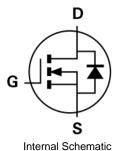
- Thermally Efficient Package Cooler Running Applications
- <1.1mm Package Profile Ideal for Thin Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (*)
- Weight: 0.097 grams (Approximate)



Top View Bottom View



Ordering Information (Note 4)

Part Number	Case	Packaging
DMT3002LPS-13	PowerDI5060-8	2,500/Tape & Reel

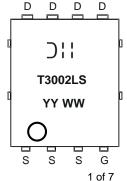
Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

Pin1

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



J;; = Manufacturer's Marking
T3002LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)

June 2016



Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±16	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	100 100	Α
Maximum Continuous Body Diode Forward Current (Not	Is	100	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	150	Α
Avalanche Current, L=3mH (Note 8)			I _{AS}	15	Α
Avalanche Energy, L=3mH (Note 8)			E _{AS}	700	mJ

Thermal Characteristics ($@T_C = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	103	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	51	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P_{D}	136	W
Thermal Resistance, Junction to Case (Note 7)		R _{0JC}	1.1	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

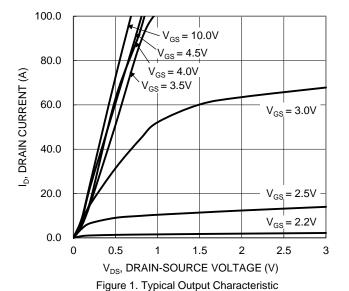
Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

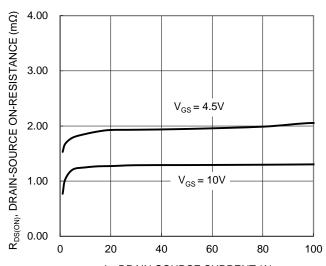
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance		_	1.25	1.6	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	2	2.5	11177	$V_{GS} = 4.5V, I_D = 25A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.1	V	$V_{GS} = 0V, I_{S} = 25A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{ISS}	_	5,000			V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	2,660		pF		
Reverse Transfer Capacitance	C _{RSS}	_	300	_			
Gate Resistance	R_{G}	_	0.75		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	37	_			
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	77	_	nC	V 45V L 25A	
Gate-Source Charge	Q _{GS}	_	10	_	IIC	$V_{DS} = 15V, I_{D} = 25A$	
Gate-Drain Charge	Q_{GD}	_	14	_			
Turn-On Delay Time	t _{D(ON)}	_	21	_			
Turn-On Rise Time	t _R	_	45	_		$V_{DD} = 15V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	32	_	ns	$I_D = 25A, R_G = 4.7\Omega$	
Turn-Off Fall Time	t _F	_	26				
Body Diode Reverse Recovery Time	t _{RR}	_	44	1	ns	In = 15A di/dt = 100A/us	
Body Diode Reverse Recovery Charge	Q _{RR}	_	52		nC	I _S = 15A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

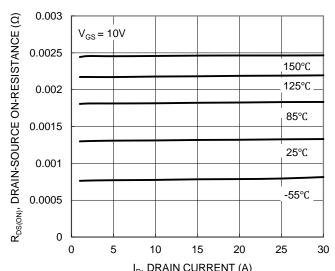
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. IAS and EAS rating are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage



I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Temperature

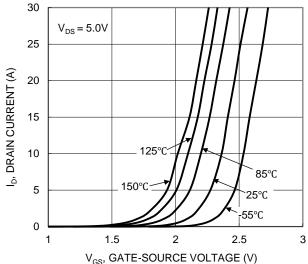
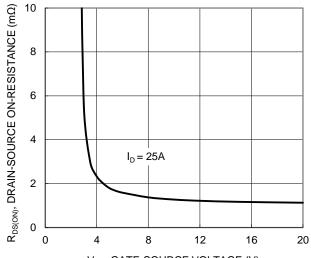
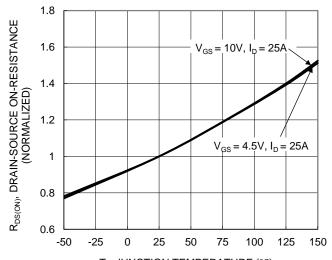


Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic



 $\rm T_{J},\,JUNCTION\,TEMPERATURE\,(^{\circ}C)$ Figure 6. On-Resistance Variation with Temperature





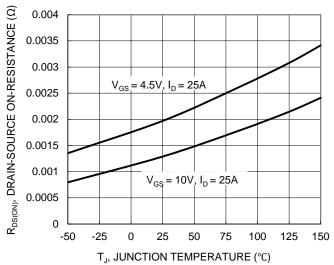


Figure 7. On-Resistance Variation with Temperature

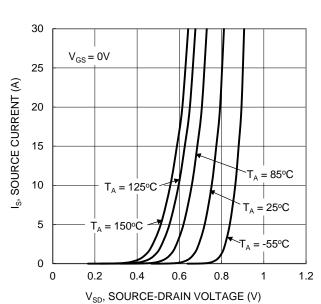
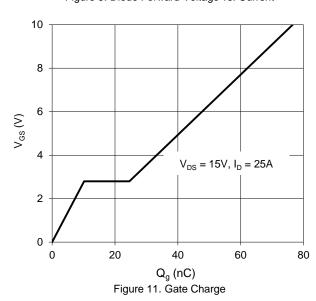
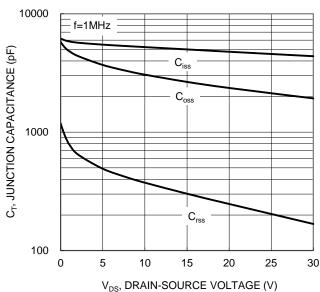


Figure 9. Diode Forward Voltage vs. Current

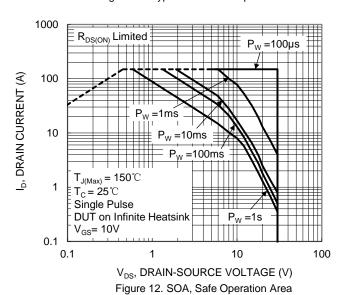


2 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 1.8 1.6 $I_D = 1mA$ 1.4 1.2 $I_{D} = 250 \mu A$ 1 8.0 0.6 0.4 0.2 25 50 75 -50 -25 100 125 150

T_J, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance





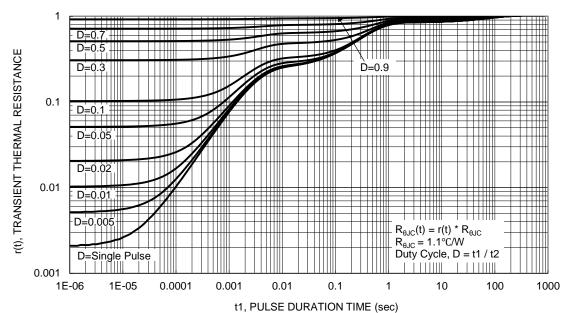


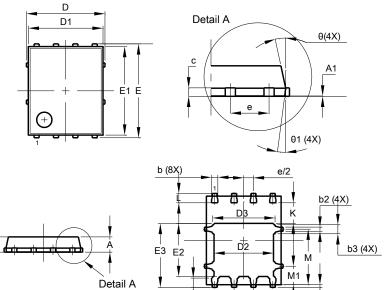
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

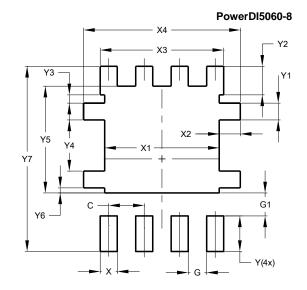
PowerDI5060-8



PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	,		
G	0.51	0.71	0.61		
K	0.51		_		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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